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Kind regards,

Team Nexperia

PHB29N08T

N-channel TrenchMOS standard level FET

Rev. 03 — 13 October 2009

Product data sheet

1. Product profile

1.1 General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product is designed and qualified for use in computing, communications, consumer and industrial applications only.

1.2 Features and benefits

- High noise immunity due to high gate threshold voltage
- Low conduction losses due to low on-state resistance

1.3 Applications

- Industrial motor control

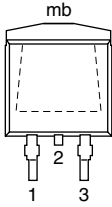
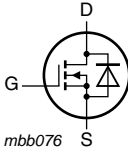
1.4 Quick reference data

Table 1. Quick reference

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25\text{ °C}; T_j \leq 175\text{ °C}$	-	-	75	V
I_D	drain current	$T_{mb} = 25\text{ °C}; V_{GS} = 11\text{ V};$ see Figure 1 and 3	-	-	27	A
P_{tot}	total power dissipation	$T_{mb} = 25\text{ °C};$ see Figure 2	-	-	88	W
Dynamic characteristics						
Q_{GD}	gate-drain charge	$V_{GS} = 10\text{ V}; I_D = 29\text{ A};$ $V_{DS} = 60\text{ V}; T_j = 25\text{ °C};$ see Figure 11	-	9	-	nC
Static characteristics						
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 11\text{ V}; I_D = 14\text{ A};$ $T_j = 175\text{ °C};$ see Figure 9 and 10	-	96	120	m Ω
		$V_{GS} = 11\text{ V}; I_D = 14\text{ A}; T_j = 25\text{ °C};$ see Figure 9 and 10	-	40	50	m Ω

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	 <p>SOT404 (D2PAK)</p>	 <p>mbb076</p>
2	D	drain [1]		
3	S	source		
mb	D	mounting base, connected to drain		

[1] It is not possible to make connection to pin 2.

3. Ordering information

Table 3. Ordering information

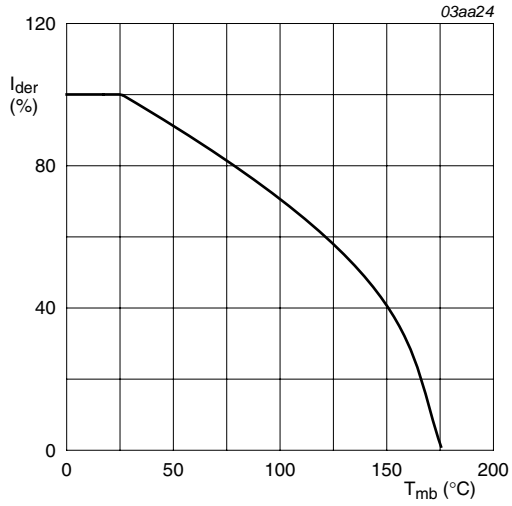
Type number	Package		Version
	Name	Description	
PHB29N08T	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

4. Limiting values

Table 4. Limiting values

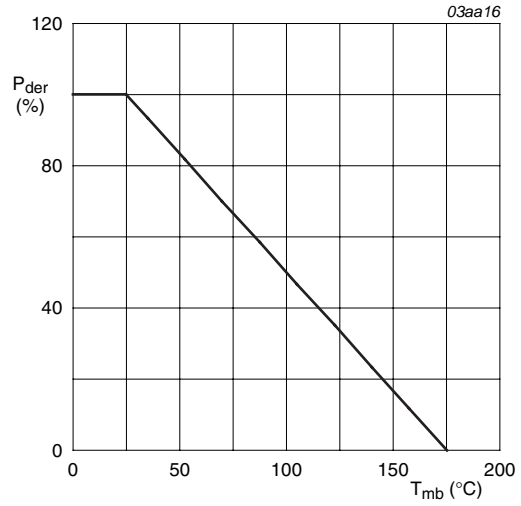
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25\text{ °C}$; $T_j \leq 175\text{ °C}$	-	75	V
V_{DGR}	drain-gate voltage	$T_j \leq 175\text{ °C}$; $T_j \geq 25\text{ °C}$; $R_{GS} = 20\text{ k}\Omega$	-	75	V
V_{GS}	gate-source voltage		-30	30	V
I_D	drain current	$V_{GS} = 11\text{ V}$; $T_{mb} = 100\text{ °C}$; see Figure 1	-	19.2	A
		$V_{GS} = 11\text{ V}$; $T_{mb} = 25\text{ °C}$; see Figure 1 and 3	-	27	A
I_{DM}	peak drain current	$t_p \leq 10\text{ }\mu\text{s}$; pulsed; $T_{mb} = 25\text{ °C}$; see Figure 3	-	108	A
P_{tot}	total power dissipation	$T_{mb} = 25\text{ °C}$; see Figure 2	-	88	W
T_{stg}	storage temperature		-55	175	°C
T_j	junction temperature		-55	175	°C
Source-drain diode					
I_S	source current	$T_{mb} = 25\text{ °C}$	-	27	A
I_{SM}	peak source current	$t_p \leq 10\text{ }\mu\text{s}$; pulsed; $T_{mb} = 25\text{ °C}$	-	108	A



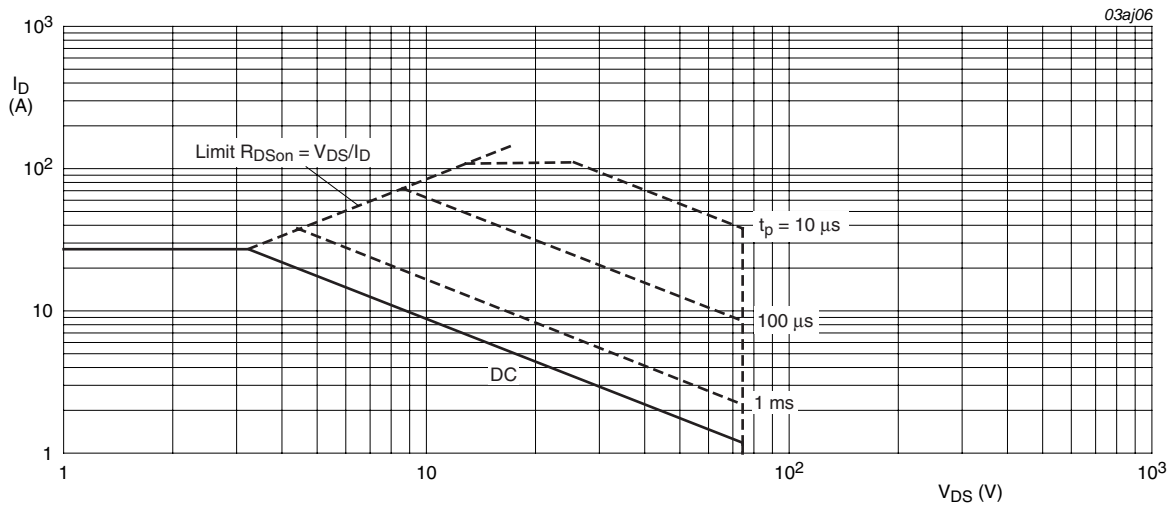
$$I_{der} = \frac{I_D}{I_{D(25^\circ\text{C})}} \times 100\%$$

Fig 1. Normalized continuous drain current as a function of mounting base temperature



$$P_{der} = \frac{P_{tot}}{P_{tot(25^\circ\text{C})}} \times 100\%$$

Fig 2. Normalized total power dissipation as a function of mounting base temperature



$T_{mb} = 25^\circ\text{C}; I_{DM}$ is single pulse; $V_{GS} = 11\text{V}$

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	-	1.7	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	SOT404 minimum footprint; mounted on a printed-circuit board	-	50	-	K/W

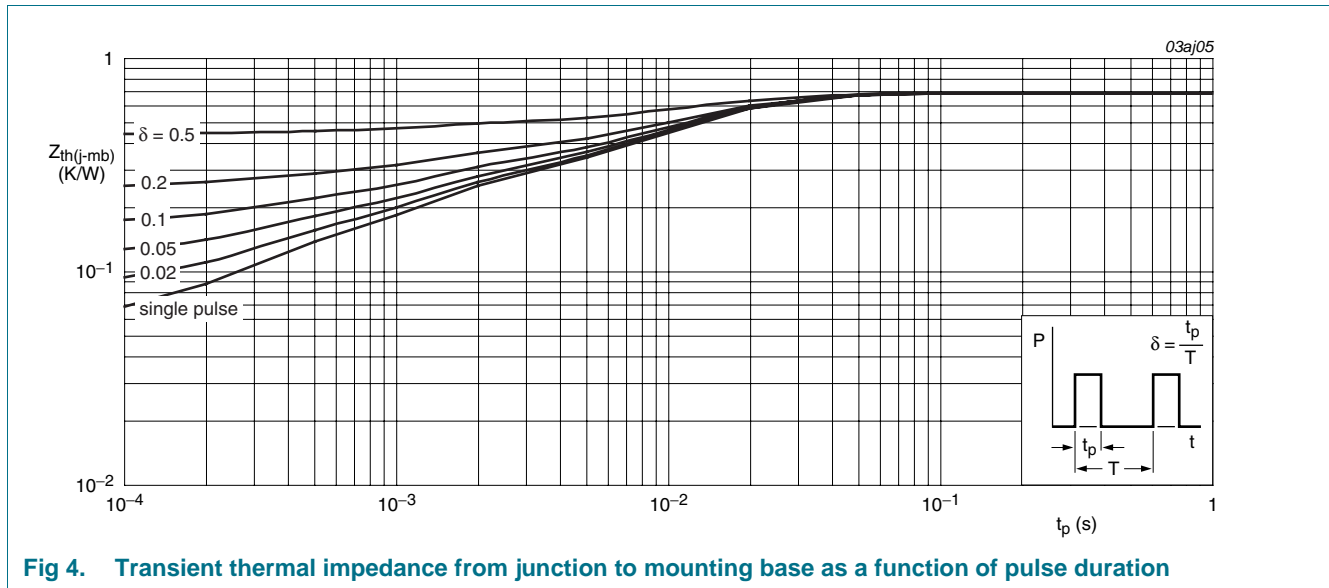
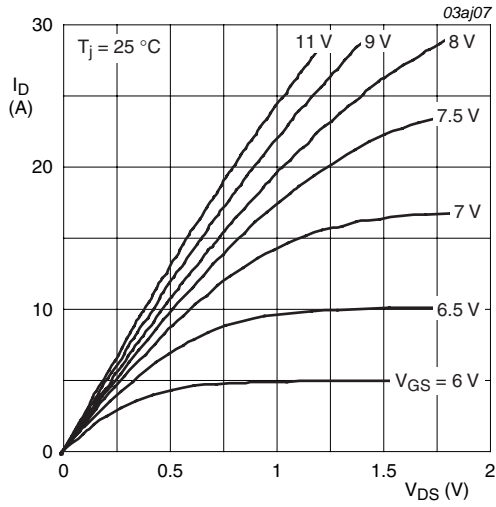


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

6. Characteristics

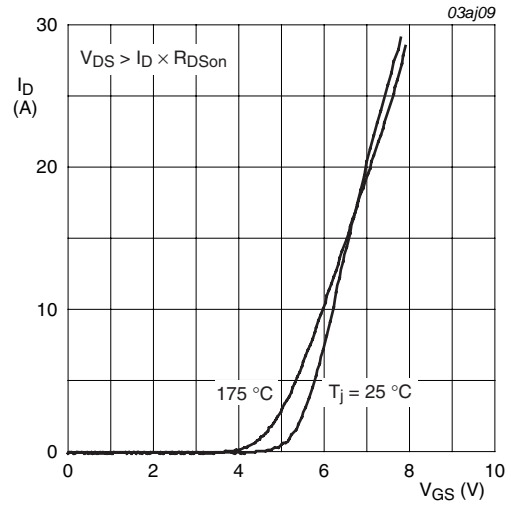
Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ }^\circ\text{C}$	70	-	-	V
		$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	75	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 2 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ }^\circ\text{C};$ see Figure 8	2.1	-	-	V
		$I_D = 2 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ }^\circ\text{C};$ see Figure 8	-	-	5.4	V
		$I_D = 2 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ }^\circ\text{C};$ see Figure 8	3	4	5	V
I_{DSS}	drain leakage current	$V_{DS} = 75 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	0.05	10	μA
		$V_{DS} = 75 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ }^\circ\text{C}$	-	-	500	μA
I_{GSS}	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	10	100	nA
		$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	10	100	nA
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 11 \text{ V}; I_D = 14 \text{ A}; T_j = 175 \text{ }^\circ\text{C};$ see Figure 9 and 10	-	96	120	m Ω
		$V_{GS} = 11 \text{ V}; I_D = 14 \text{ A}; T_j = 25 \text{ }^\circ\text{C};$ see Figure 9 and 10	-	40	50	m Ω
Dynamic characteristics						
$Q_{G(tot)}$	total gate charge	$I_D = 29 \text{ A}; V_{DS} = 60 \text{ V}; V_{GS} = 10 \text{ V};$ $T_j = 25 \text{ }^\circ\text{C};$ see Figure 11	-	19	-	nC
Q_{GS}	gate-source charge		-	6	-	nC
Q_{GD}	gate-drain charge		-	9	-	nC
C_{iss}	input capacitance	$V_{DS} = 25 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ }^\circ\text{C};$ see Figure 12	-	810	-	pF
C_{oss}	output capacitance		-	140	-	pF
C_{rss}	reverse transfer capacitance		-	85	-	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 38 \text{ V}; R_L = 1.3 \text{ } \Omega; V_{GS} = 10 \text{ V};$ $R_{G(ext)} = 5.6 \text{ } \Omega; T_j = 25 \text{ }^\circ\text{C}; I_D = 29 \text{ A}$	-	9.5	-	ns
t_r	rise time		-	70	-	ns
$t_{d(off)}$	turn-off delay time		-	15	-	ns
t_f	fall time		-	9	-	ns
Source-drain diode						
V_{SD}	source-drain voltage	$I_S = 14 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C};$ see Figure 13	-	0.95	1.2	V
t_{rr}	reverse recovery time	$I_S = 14 \text{ A}; di_S/dt = -100 \text{ A}/\mu\text{s}; V_{GS} = 0 \text{ V};$ $V_{DS} = 25 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	50	-	ns
Q_r	recovered charge		-	65	-	nC



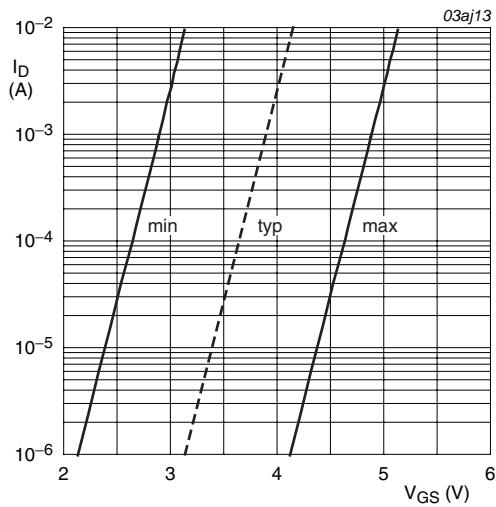
$T_j = 25^\circ\text{C}$

Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values



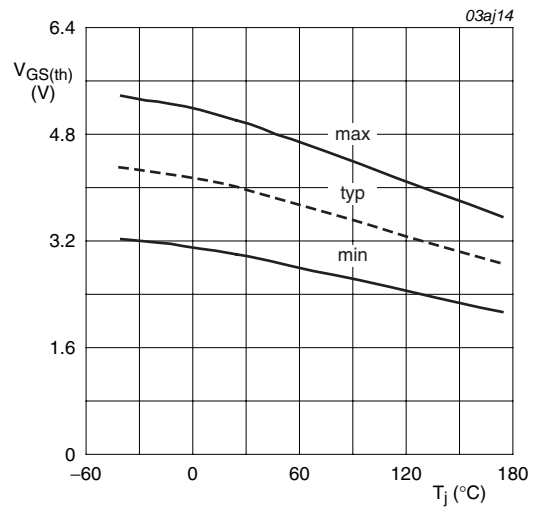
$T_j = 25^\circ\text{C}$ and $175^\circ\text{C}; V_{DS} > I_D \times R_{DSon}$

Fig 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values



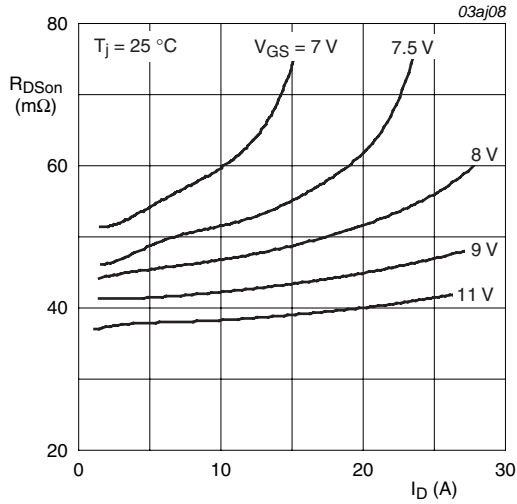
$T_j = 25^\circ\text{C}; V_{DS} = 10\text{V}$

Fig 7. Sub-threshold drain current as a function of gate-source voltage



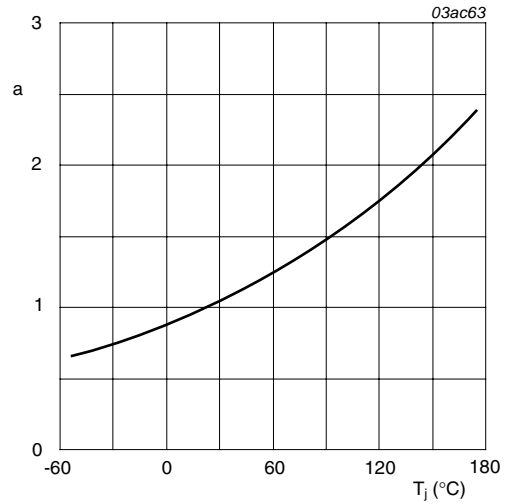
$I_D = 2\text{mA}; V_{DS} = V_{GS}$

Fig 8. Gate-source threshold voltage as a function of junction temperature



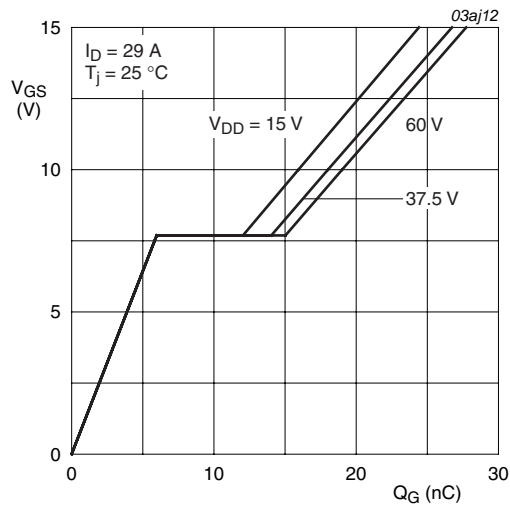
$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

Fig 9. Drain-source on-state resistance as a function of drain current; typical value



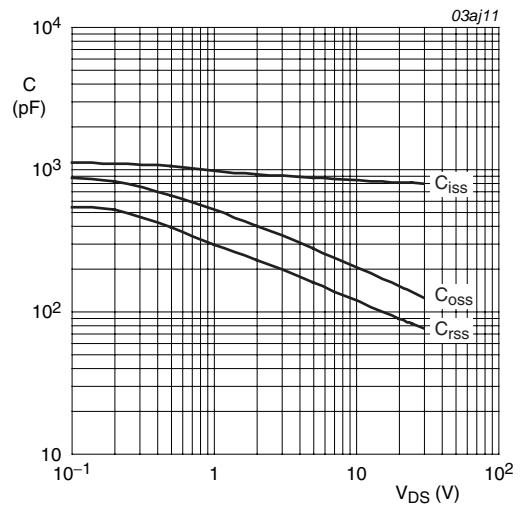
$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

Fig 10. Normalized drain-source on-state resistance factor as a function of junction temperature



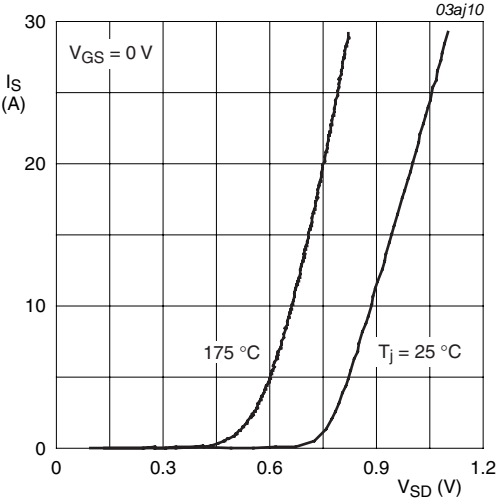
$$I_D = 29A; V_{DS} = 15V, 37.5V \text{ and } 60V$$

Fig 11. Gate-source voltage as a function of gate charge; typical values



$$V_{GS} = 0V; f = 1MHz$$

Fig 12. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



$T_j = 25^\circ\text{C}$ and $175^\circ\text{C}; V_{GS} = 0\text{V}$

Fig 13. Source current as a function of source-drain voltage; typical values

7. Package outline

Plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)

SOT404

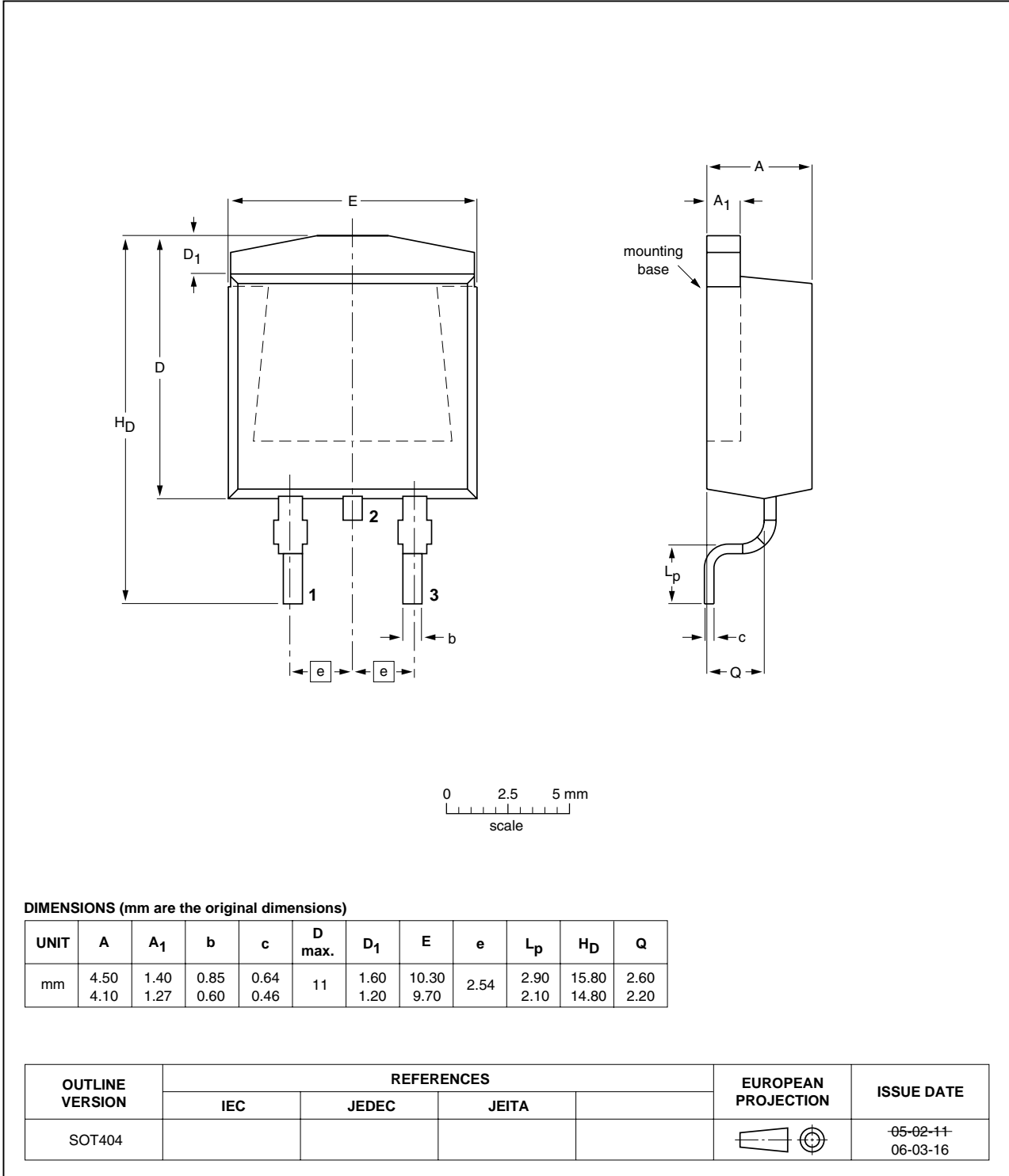


Fig 14. Package outline SOT404 (D2PAK)

8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PHB29N08T_3	20091013	Product data sheet	-	PHB29N08T_2
Modifications:	• Various changes to content.			
PHB29N08T_2	20090310	Product data sheet	-	PHP_PHB29N08T-01
PHP_PHB29N08T-01 (9397 750 09651)	20020529	Product data	-	-

9. Legal information

9.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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